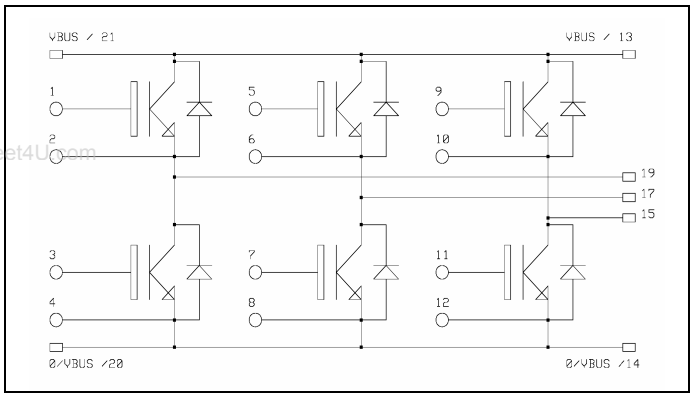
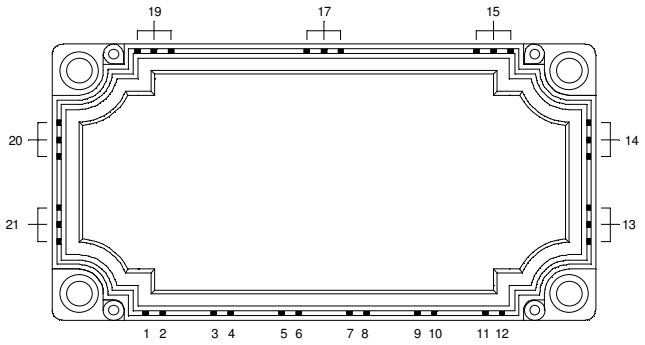
APTGS75X170E3

3 Phase bridge
NPT IGBT Power Module

V_{CES} = 1700V
I_C = 75A @ Tc = 80°C





Application

- AC Motor control

Features

- Non Punch Through (NPT) Low Loss IGBT®
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - Avalanche energy rated
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Breakdown Voltage		1700	V
I_C	Continuous Collector Current	T_C = 25°C	150	A
		T_C = 80°C	75	
I_{CM}	Pulsed Collector Current	T_C = 25°C	250	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	T_C = 25°C	625	W
RBSOA	Reverse Bias Operating Area	T_j = 125°C	150A@1600V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed.

Electrical Characteristics

All ratings @ T_j = 25°C unless otherwise specified

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
BV_{CES}	Collector - Emitter Breakdown Voltage	V_{GE} = 0V, I_C = 1mA		1700			V
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V V_{CE} = 1700V	T_j = 25°C		0.03	0.15	mA
			T_j = 125°C		2		
$V_{CE(on)}$	Collector Emitter on Voltage	V_{GE} =15V I_C = 75A	T_j = 25°C		2.7	3.3	V
			T_j = 125°C		3.2		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE} , I_C = 3.5 mA		4.5		6.5	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	V_{GE} = 0V, V_{CE} = 25V f = 1MHz		5000		pF
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = ±15V V_{Bus} = 900V I_C = 75A R_G = 20Ω		100		ns
T_r	Rise Time			100		
$T_{d(off)}$	Turn-off Delay Time			800		
T_f	Fall Time			30		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) V_{GE} = ±15V V_{Bus} = 900V I_C = 75A R_G = 20Ω		100		ns
T_r	Rise Time			100		
$T_{d(off)}$	Turn-off Delay Time			900		
T_f	Fall Time			30		
E_{off}	Turn off Energy			22		mJ

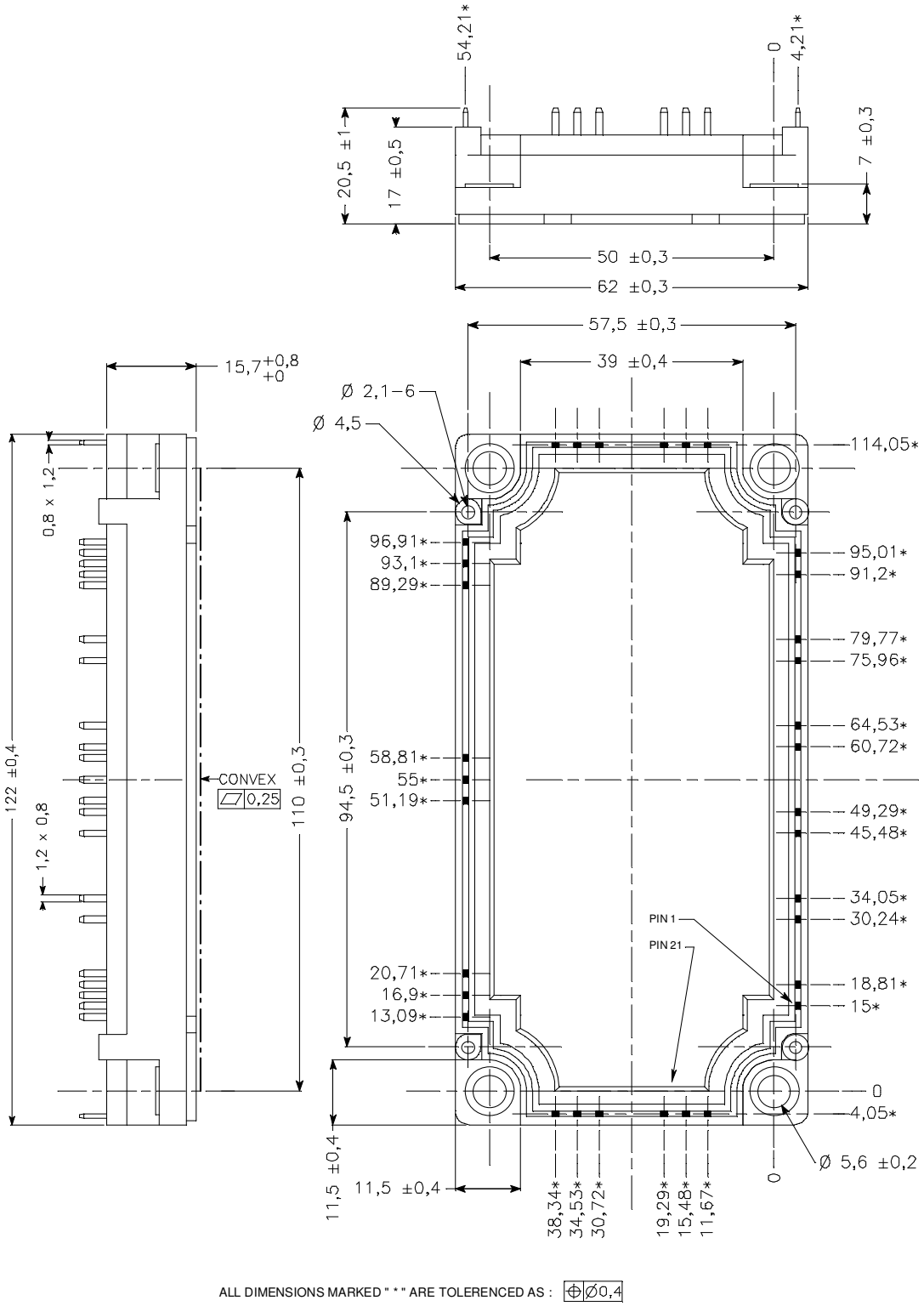
Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_F	Diode Forward Voltage	I_F = 75A V_{GE} = 0V	T_j = 25°C		2.2	2.6	V
			T_j = 125°C		2.0		
E_r	Reverse Recovery Energy	I_F = 75A V_R = 900V di/dt =900A/µs	T_j = 25°C		3.5		mJ
			T_j = 125°C		6.5		
Q_{rr}	Reverse Recovery Charge	I_F = 75A V_R = 900V di/dt =900A/µs	T_j = 25°C		9		µC
			T_j = 125°C		19		

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R_{thJC}	Junction to Case		IGBT			0.2	°C/W
			Diode			0.47	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		125	
Torque	Mounting torque	To Heatsink	M5	3		4.5	N.m
Wt	Package Weight					300	g

Package outline



ALL DIMENSIONS MARKED " * " ARE TOLERENCED AS : ⌖ Ø0,4

APT reserves the right to change, without notice, the specifications and information contained herein